

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity. The "very sensitive gate" "series D" is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with very sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Electronic thermostats
- General purpose motor controls

4. Quick reference data

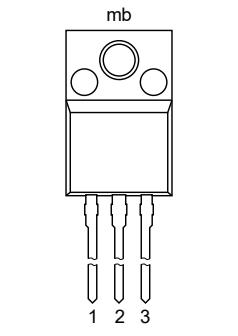
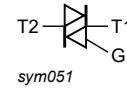
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	65	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	-	71	A
T_j	junction temperature		-	-	125	$^\circ\text{C}$
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	5	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_2 - G -$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	-	5	mA
I_H	holding current	$V_D = 12 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 9		-	-	6	mA
V_T	on-state voltage	$I_T = 10 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 10		-	1.3	1.65	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402 \text{ V}$; $T_j = 110 \text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		20	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 10 \text{ V}/\mu\text{s}$; gate open circuit; Fig. 12		2	-	-	A/ms
		$V_D = 400 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 0.1 \text{ V}/\mu\text{s}$; gate open circuit; Fig. 12		6	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 TO-220F (SOT186A)	 sym051
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package			Version
	Name	Description		
BTA208X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"		SOT186A

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5		-	65	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$		-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN		-	21	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 0.2\text{ A}$		-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	$^\circ\text{C}$
T_j	junction temperature			-	125	$^\circ\text{C}$

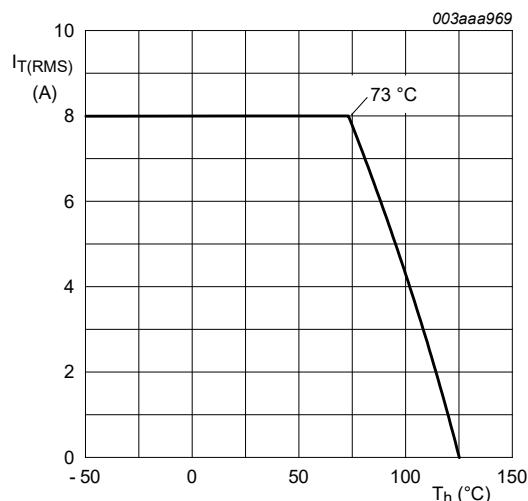


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

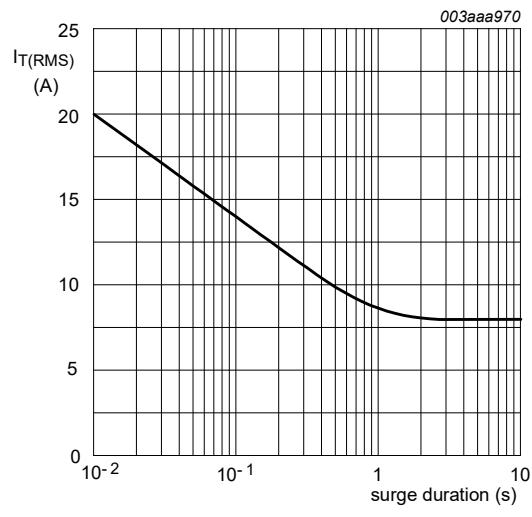


Fig. 2. RMS on-state current as a function of surge duration; maximum values

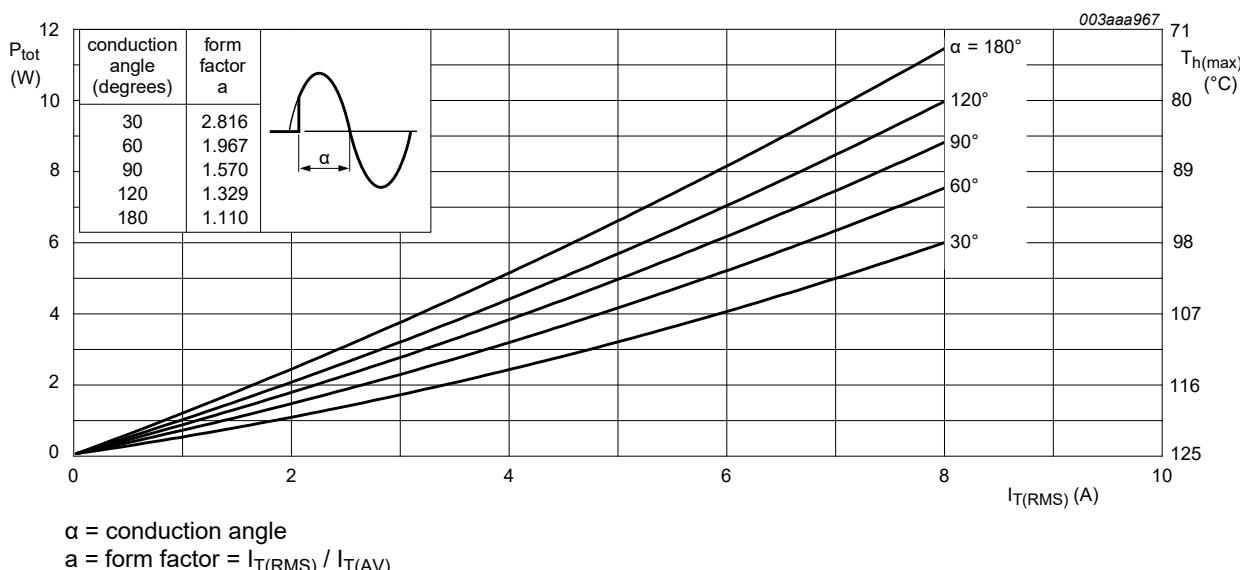


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

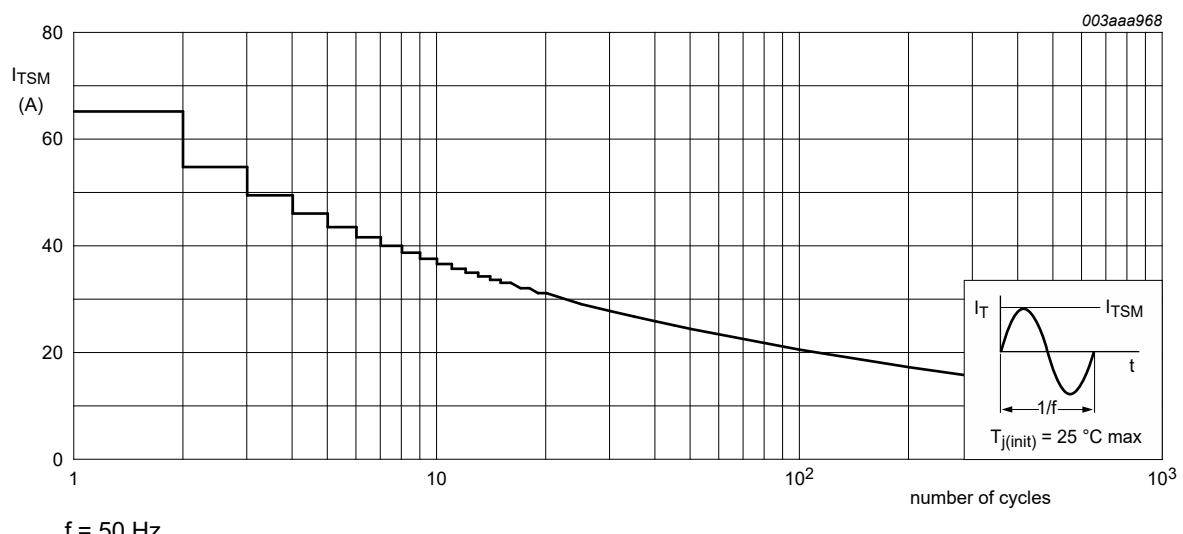


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

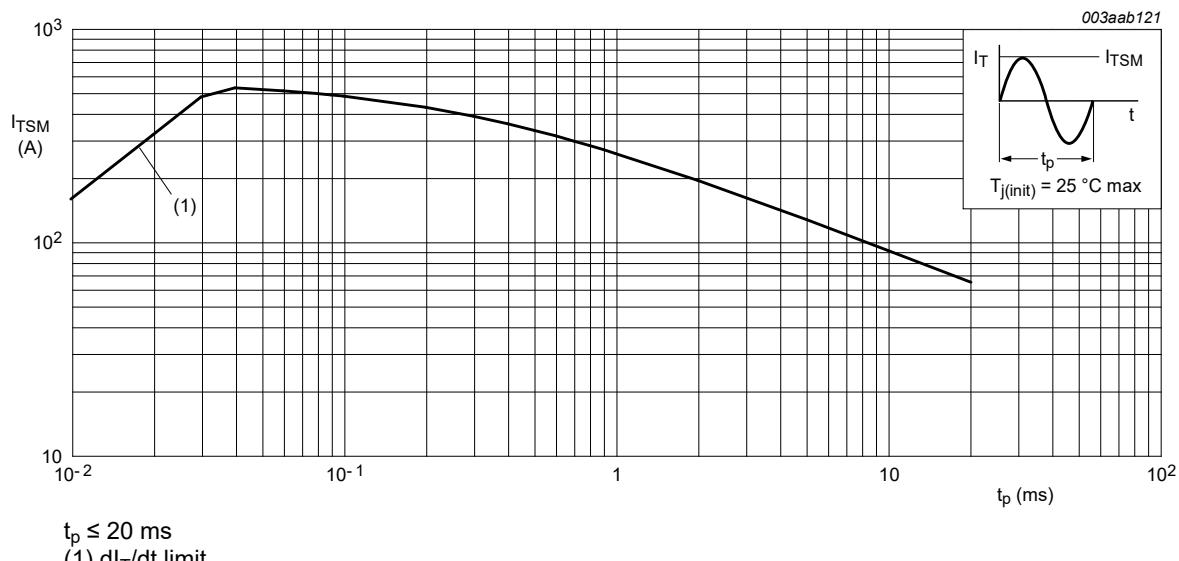
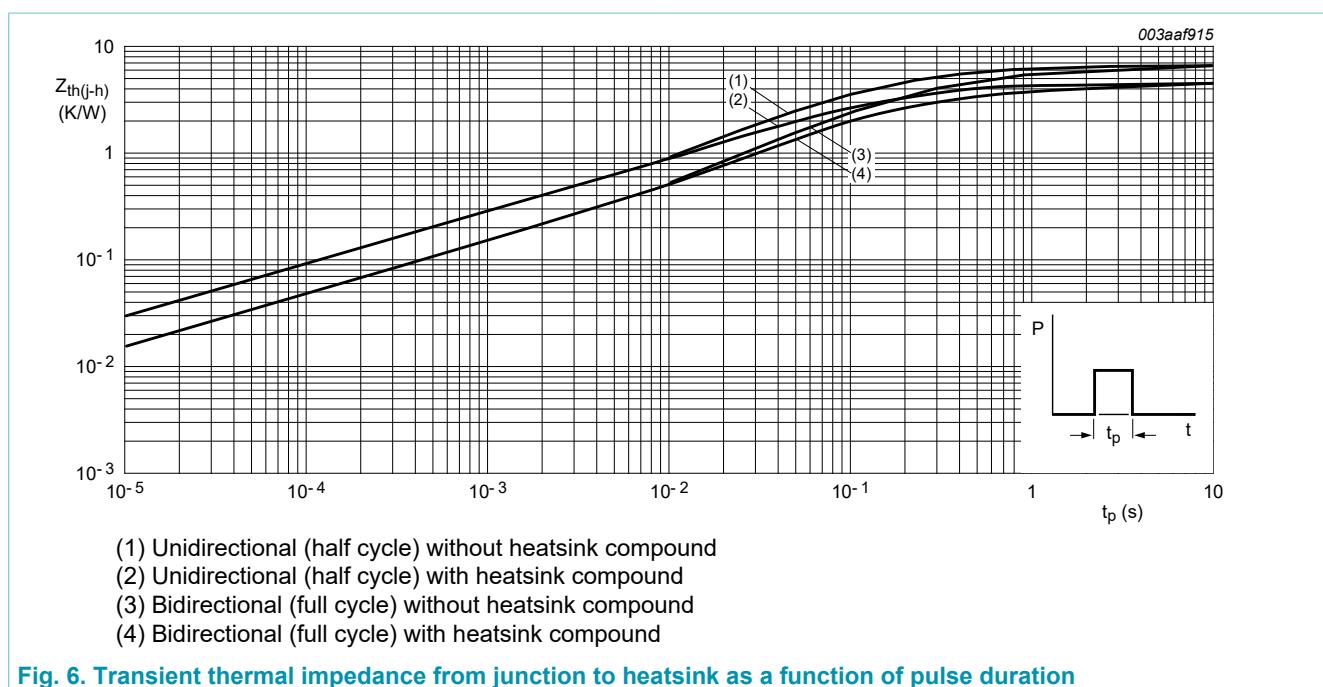


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; Fig. 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50 \text{ Hz} \leq f \leq 60 \text{ Hz}$; $\text{RH} \leq 65\%$; $T_h = 25^\circ\text{C}$	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1 \text{ MHz}$; $T_h = 25^\circ\text{C}$	-	10	-	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_2+ \text{ G+}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	-	5	mA
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_2+ \text{ G-}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	-	5	mA
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_2- \text{ G-}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	-	5	mA
I_L	latching current	$V_D = 12 \text{ V}$; $I_G = 0.1 \text{ A}$; $T_2+ \text{ G+}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 8		-	-	6	mA
		$V_D = 12 \text{ V}$; $I_G = 0.1 \text{ A}$; $T_2+ \text{ G-}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 8		-	-	9	mA
		$V_D = 12 \text{ V}$; $I_G = 0.1 \text{ A}$; $T_2- \text{ G-}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 8		-	-	6	mA
I_H	holding current	$V_D = 12 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 9		-	-	6	mA
V_T	on-state voltage	$I_T = 10 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 10		-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 11		-	0.7	1	V
		$V_D = 400 \text{ V}$; $I_T = 0.1 \text{ A}$; $T_j = 125 \text{ }^\circ\text{C}$; Fig. 11		0.25	0.4	-	V
I_D	off-state current	$V_D = 600 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402 \text{ V}$; $T_j = 110 \text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		20	-	-	V/μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 10 \text{ V/}\mu\text{s}$; gate open circuit; Fig. 12		2	-	-	A/ms
		$V_D = 400 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 0.1 \text{ V/}\mu\text{s}$; gate open circuit; Fig. 12		6	-	-	A/ms

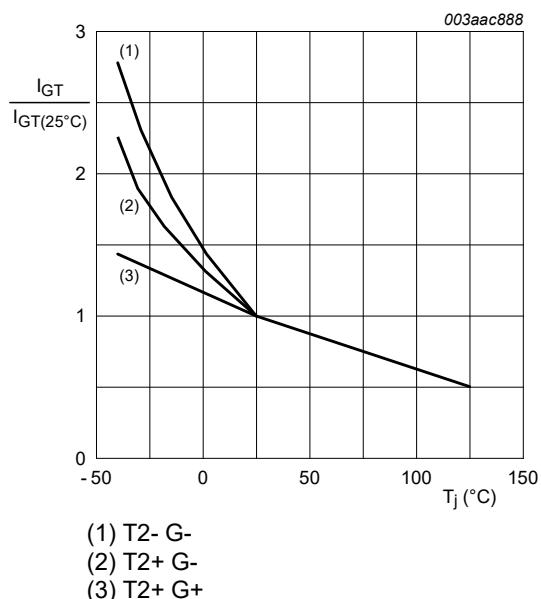


Fig. 7. Normalized gate trigger current as a function of junction temperature

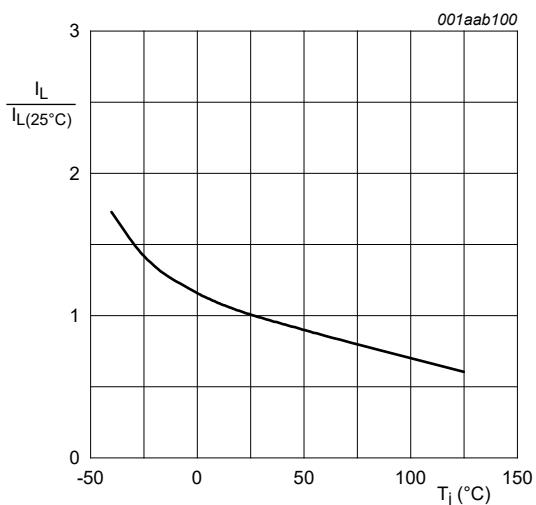


Fig. 8. Normalized latching current as a function of junction temperature

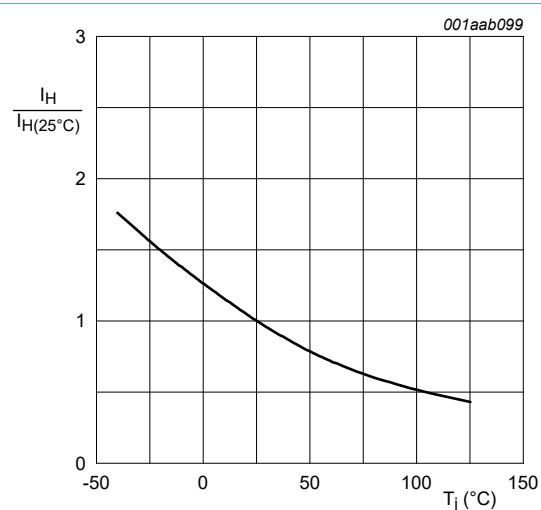


Fig. 9. Normalized holding current as a function of junction temperature

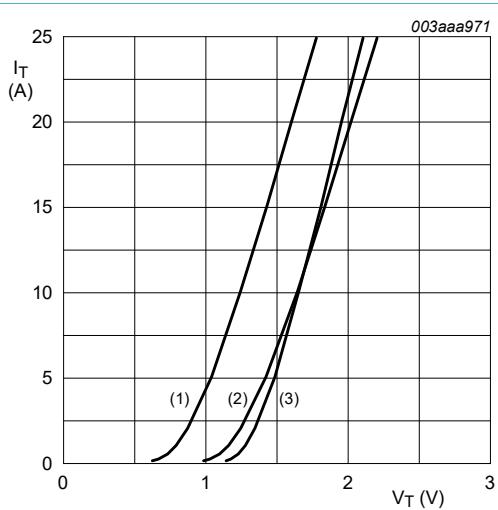


Fig. 10. On-state current as a function of on-state voltage

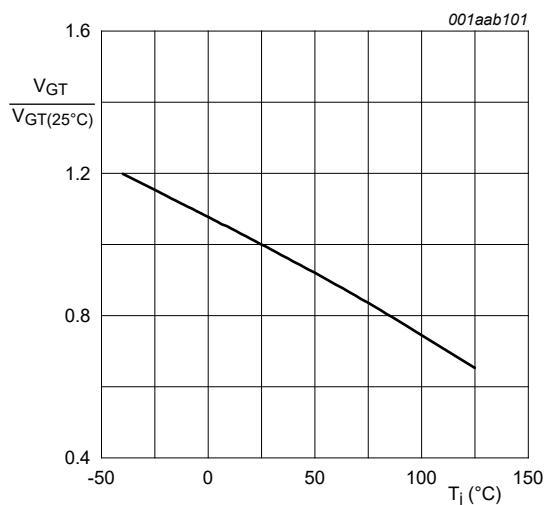


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

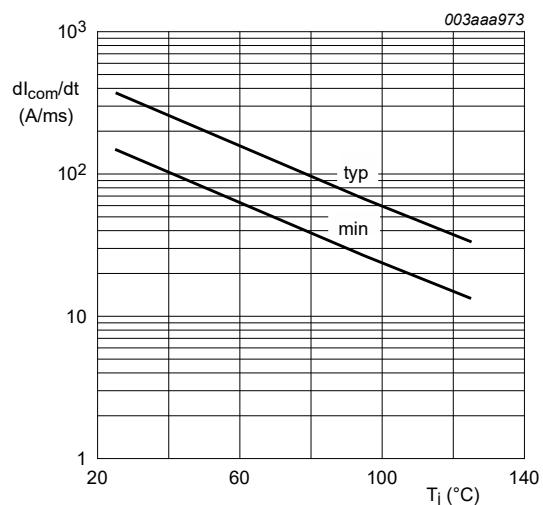


Fig. 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

11. Package outline

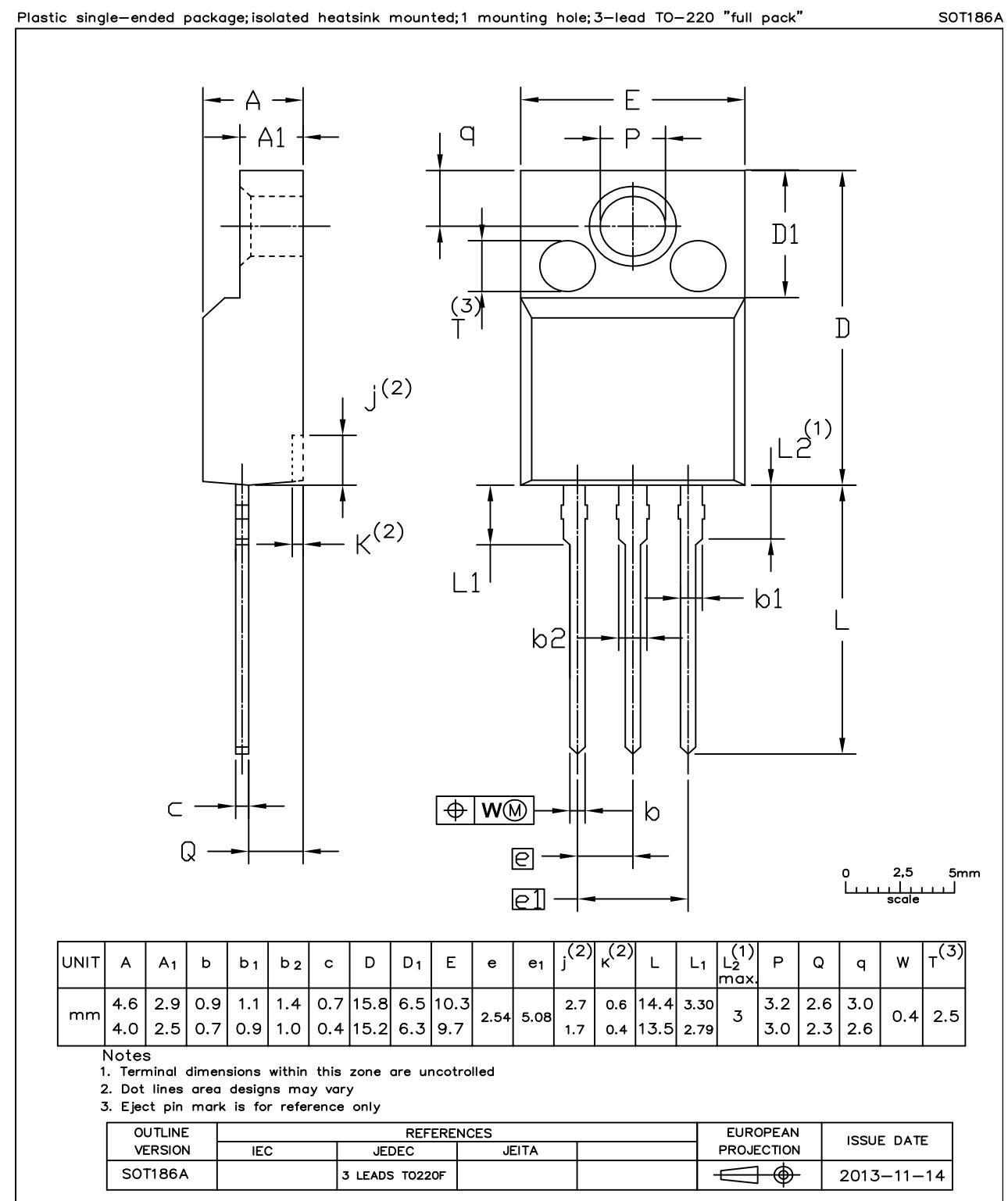


Fig. 13. Package outline TO-220F (SOT186A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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